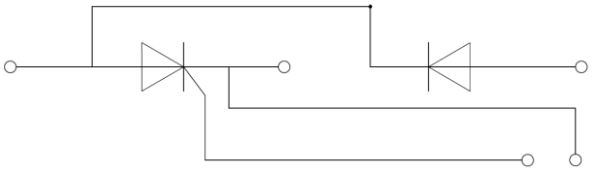
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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

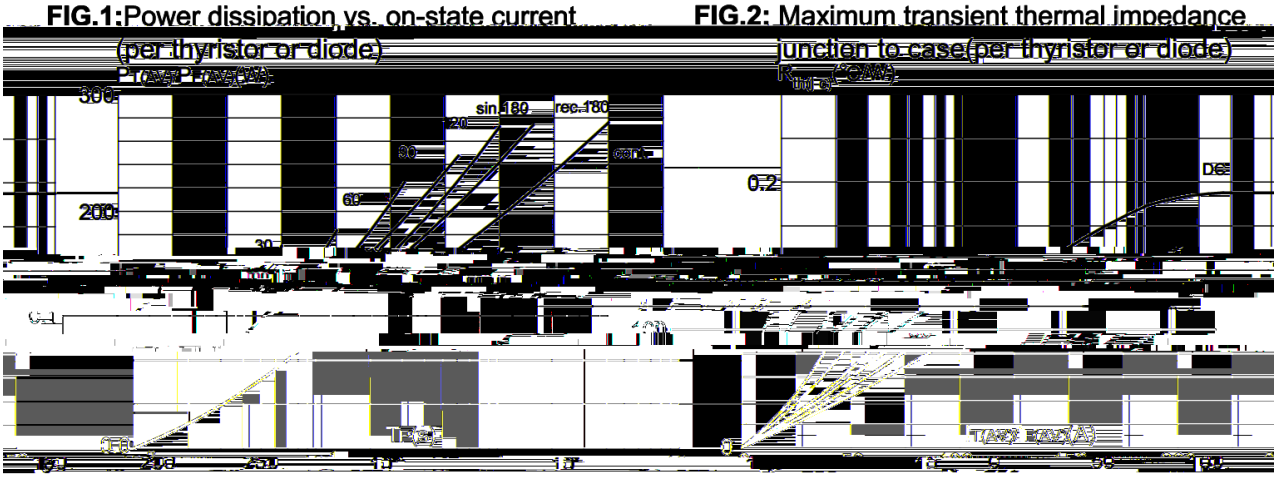


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)



FIG.5 Gate trigger characteristics

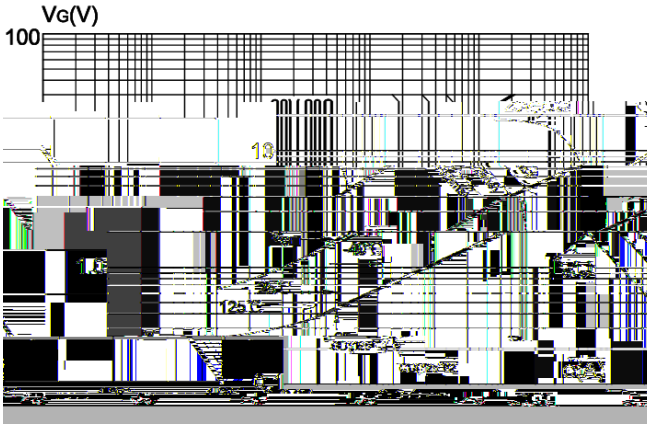
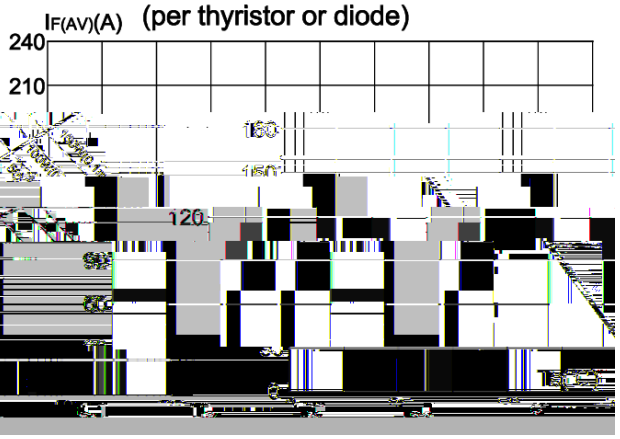
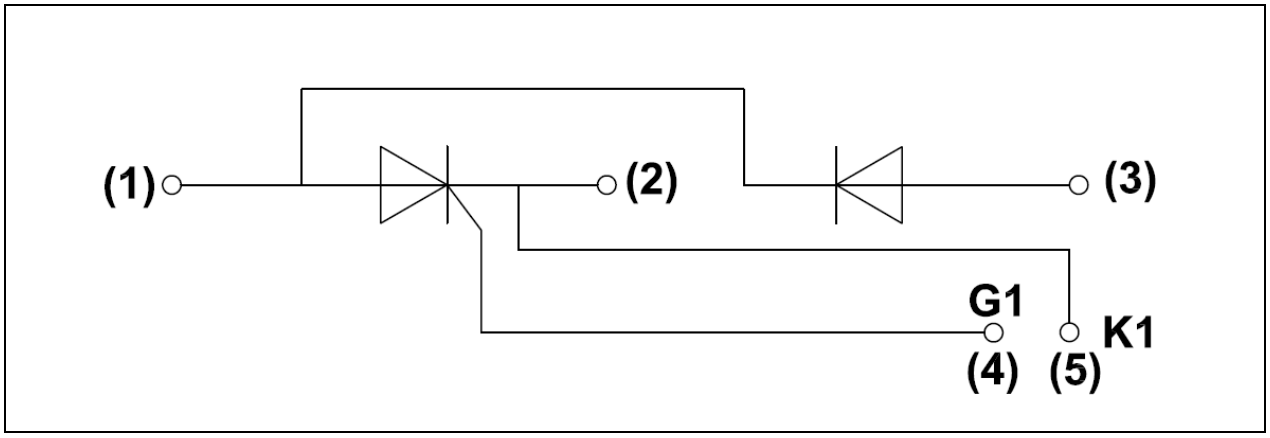
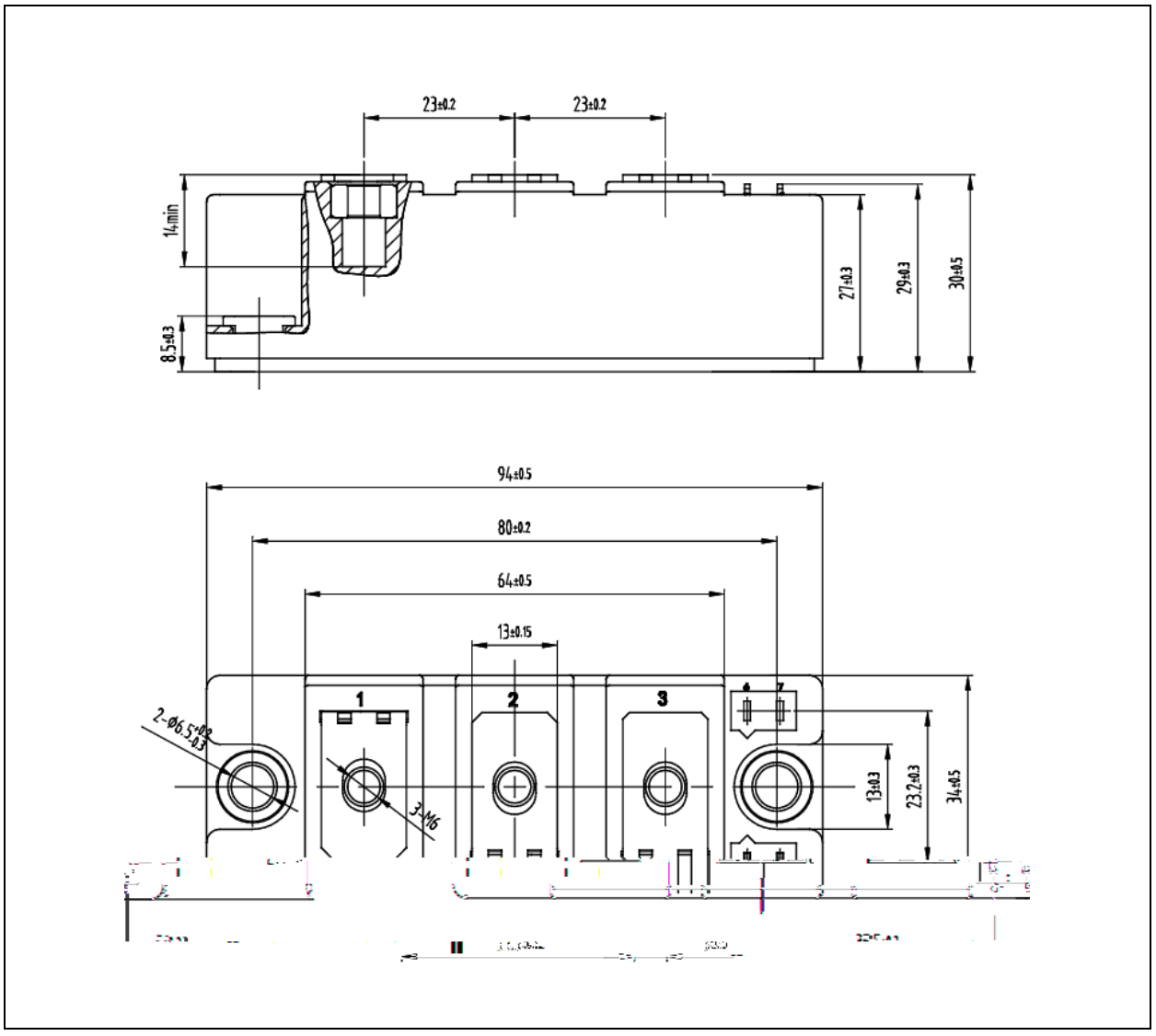


FIG.6: Forward current vs. case temperature (per thyristor or diode)



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(1)
(2)
(3)
G1
K1
(4)
(5)


23±0.2
23±0.2
14min
8.5±0.3
27±0.3
29±0.3
30±0.5
94±0.5
80±0.2
64±0.5
13±0.15
1
2
3
2-Ø6.5±0.3
3-M6
13±0.3
23.2±0.3
34±0.5